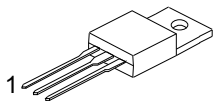
NJ6N65 POWER MOSFET

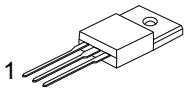
6.2A 650V N-CHANNEL POWER MOSFET

■ DESCRIPTION

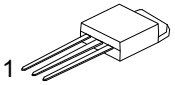
The NJ6N65 is a high voltage power MOSFET designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and high rugged avalanche characteristics. This power MOSFET is usually used in high speed switching applications of switching power supplies and adaptors.



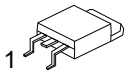
TO-220



TO-220F



TO-251

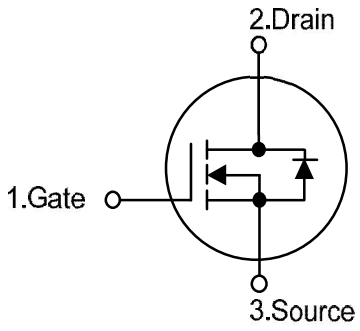


TO-252

■ FEATURES

* V_{DS} = 650V
* I_D = 6.2A
* RDS(ON) = 1.7 ohm@VGS = 10V
* Ultra low gate charge (typical 20 nC)
* Low reverse transfer Capacitance (CRSS = typical 10pF)
* Fast switching capability
* Avalanche energy tested
* Improved dv/dt capability, high ruggedness

■ SYMBOL



■ ORDERING INFORMATION

Ordering Number	Package	Pin Assignment			Packing
		1	2	3	
NJ6N65-LI	TO-220	G	D	S	Tape Box
NJ6N65-BL	TO-220	G	D	S	Bulk
NJ6N65F-LI	TO-220F	G	D	S	Tube
NJ6N65A-LI	TO-251	G	D	S	Tube
NJ6N65D-TR	TO-252	G	D	S	Tape Ree
NJ6N65D-LI	TO-252	G	D	S	Tube

Note: Pin Assignment: G: Gate D: Drain S: Source

NJ6N65 POWER MOSFET

■ ABSOLUTE MAXIMUM RATINGS (T_C = 25°C, unless otherwise specified)

PARAMETER			SYMBOL	RATINGS	UNIT
Drain-Source Voltage			V_{DSS}	650	V
Gate-Source Voltage			V_{GSS}	±30	V
Avalanche Current (Note 2)			I_{AR}	6.2	A
Continuous Drain Current			I_D	6.2	A
Pulsed Drain Current (Note 2)			I_{DM}	24.8	A
Avalanche Energy	Single Pulsed (Note 3)	6N65	E_{AS}	440	mJ
		6N65-P		180	
Peak Diode Recovery dv/dt (Note 4)			dv/dt	4.5	ns
Power Dissipation	TO-220		P_D	125	W
	TO-220F			40	W
	TO-251/TO-252			55	W
Junction Temperature			T_J	+150	°C
Operating Temperature			T_{OPR}	-55 ~ +150	°C
Storage Temperature			T_{STG}	-55 ~ +150	°C

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.
2. Repetitive Rating : Pulse width limited by T_J
3. L = 14mH, I_{AS} = 6A, V_{DD} = 90V, R_G = 25 Ω, Starting T_J = 25°C
4. I_{SD} ≤ 6.2A, di/dt ≤200A/μs, V_{DD} ≤ BV_{DSS}, Starting T_J = 25°C

■ THERMAL DATA

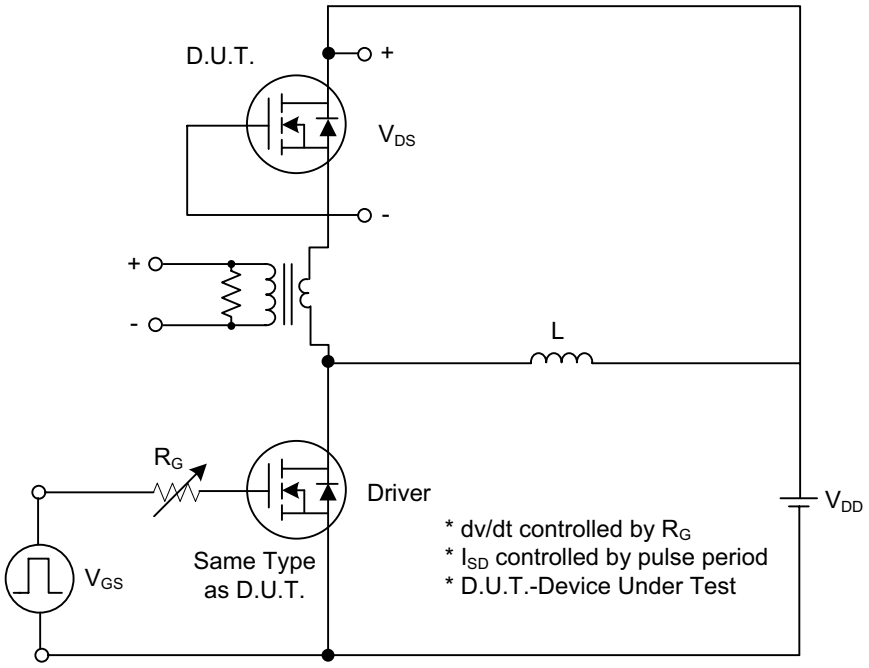
PARAMETER		SYMBOL	RATING	UNIT
Junction to Ambient	TO-220	θ_{JA}	62.5	°C/W
	TO-220F		62.5	°C/W
	TO-251/TO-252		110	°C/W
Junction to Case	TO-220	θ_{JC}	1.0	°C/W
	TO-220F		3.2	°C/W
	TO-251/TO-252		2.27	°C/W

■ ELECTRICAL CHARACTERISTICS (T_J=25°C, unless otherwise specified)

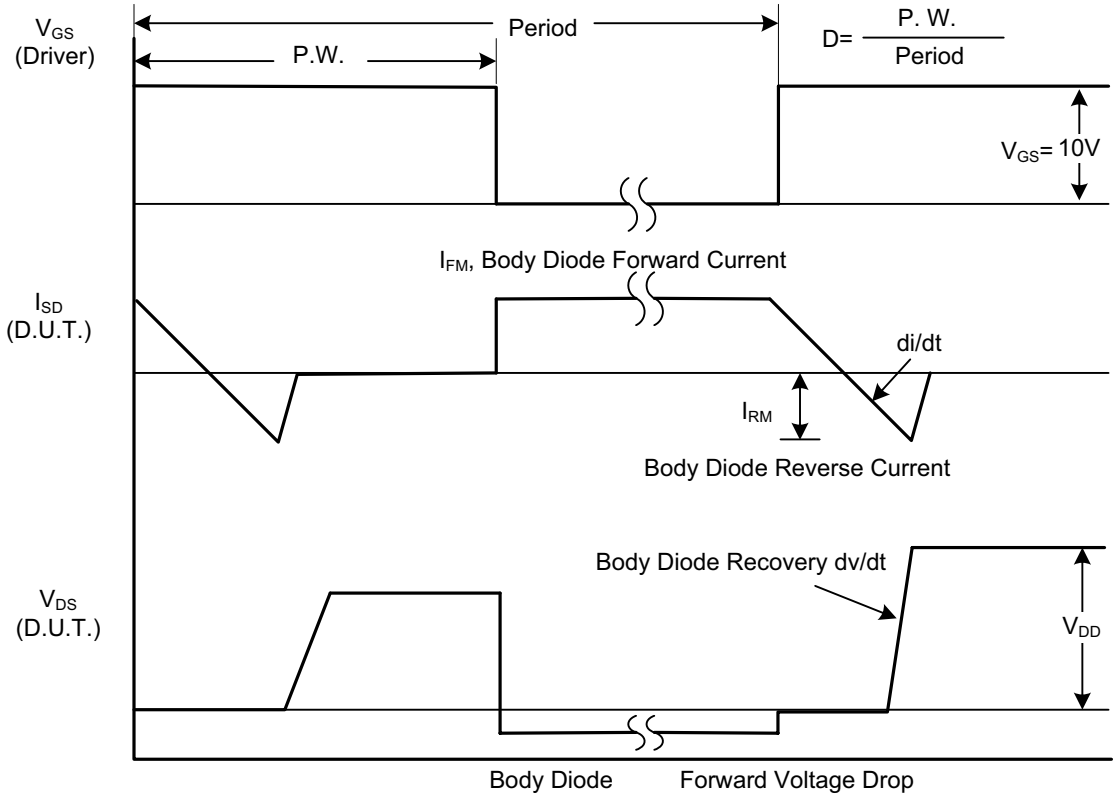
PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage		BV_{DSS}	V_{GS} = 0V, I_D = 250μA	650			V
Drain-Source Leakage Current		I_{DSS}	V_{DS} = 650V, V_{GS} = 0V			10	μA
Gate- Source Leakage Current	Forward	I_{GSS}	V_{GS} = 30V, V_{DS} = 0V			100	nA
	Reverse		V_{GS} = -30V, V_{DS} = 0V			-100	nA
Breakdown Voltage Temperature Coefficient		$\triangle BV_{DSS}/\triangle T_J$	I_D=250μA, Referenced to 25°C		0.53		V/°C
ON CHARACTERISTICS							
Gate Threshold Voltage		$V_{GS(TH)}$	V_{DS} = V_{GS}, I_D = 250μA	2.0		4.0	V
Static Drain-Source On-State Resistance	6N65	$R_{DS(ON)}$	V_{GS} = 10V, I_D = 3.1A		1.1	1.7	Ω
	6N65-P				1.4	2	Ω
DYNAMIC CHARACTERISTICS							
Input Capacitance	6N65	C_{ISS}	V_{DS}=25V, V_{GS}=0V, f=1.0 MHz		800	1000	pF
	6N65-P				770	1000	pF
Output Capacitance	6N65	C_{OSS}			95	120	pF
	6N65-P				70	120	pF
Reverse Transfer Capacitance	6N65	C_{RSS}			18	25	pF
	6N65-P				10	25	pF
SWITCHING CHARACTERISTICS							
Turn-On Delay Time		$t_{D(ON)}$	V_{DD}=325V, I_D =6.2A, R_G =25Ω (Note 1, 2)		20	50	ns
Turn-On Rise Time	6N65	t_R			100	120	ns
	6N65-P				70	120	ns
Turn-Off Delay Time		$t_{D(OFF)}$			40	90	ns
Turn-Off Fall Time	6N65	t_F			120	150	ns
	6N65-P				80	150	ns
Total Gate Charge		Q_G	V_{DS}=520V, I_D=6.2A, V_{GS}=10V (Note 1, 2)		20	25	nC
Gate-Source Charge		Q_{GS}			4.9		nC
Gate-Drain Charge		Q_{GD}			9.4		nC
DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS							
Drain-Source Diode Forward Voltage		V_{SD}	V_{GS} = 0 V, I_S = 6.2 A			1.4	V
Maximum Continuous Drain-Source Diode Forward Current		I_S				6.2	A
Maximum Pulsed Drain-Source Diode Forward Current		I_{SM}				24.8	A
Reverse Recovery Time		t_{RR}	V_{GS} = 0 V, I_S = 6.2 A, dI_F/dt = 100 A/μs (Note 1)		290		ns
Reverse Recovery Charge		Q_{RR}			2.35		μC

Notes: 1. Pulse Test: Pulse width ≤ 300μs, Duty cycle ≤ 2%
2. Essentially independent of operating temperature

■ TEST CIRCUITS AND WAVEFORMS

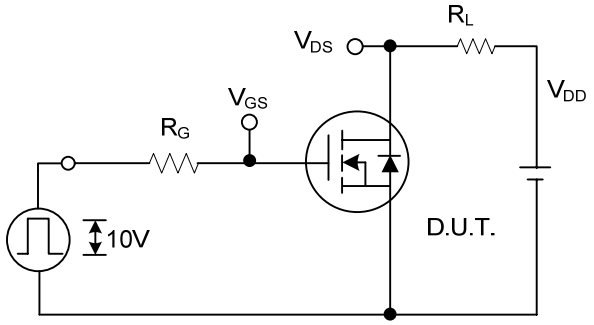


Peak Diode Recovery dv/dt Test Circuit

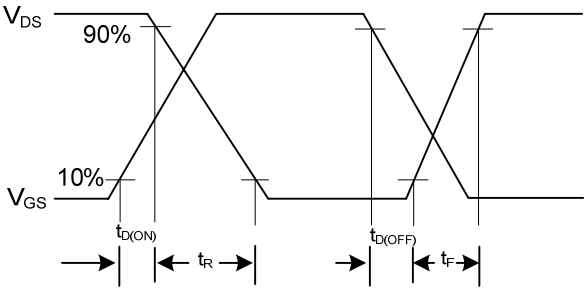


Peak Diode Recovery dv/dt Waveforms

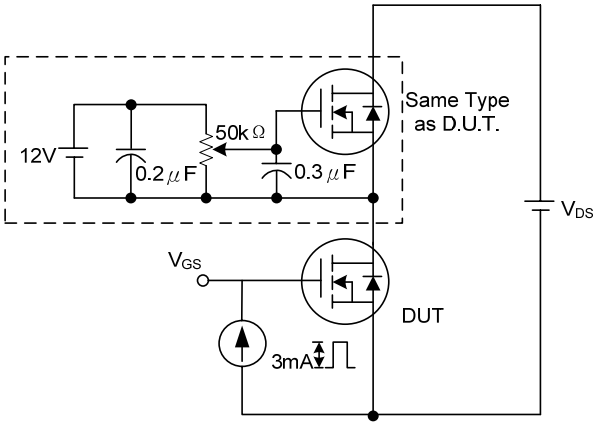
■ TEST CIRCUITS AND WAVEFORMS (Cont.)



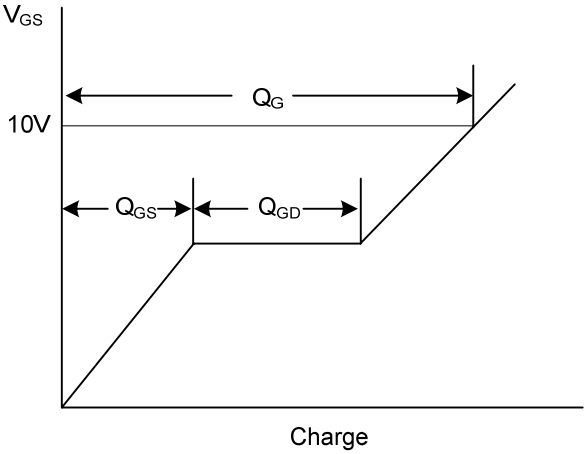
Switching Test Circuit



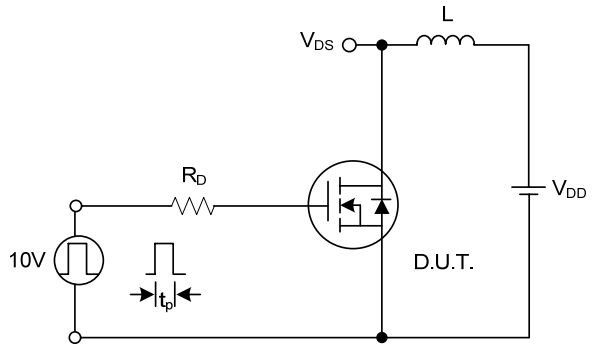
Switching Waveforms



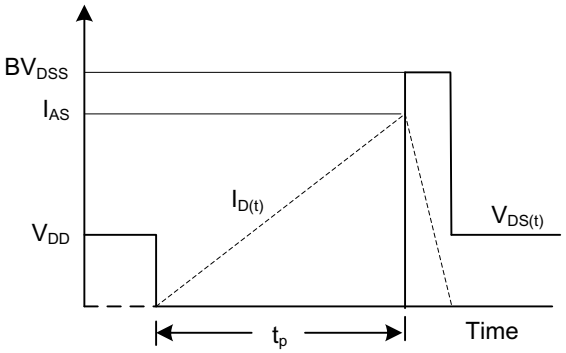
Gate Charge Test Circuit



Gate Charge Waveform



Unclamped Inductive Switching Test Circuit



Unclamped Inductive Switching Waveforms

■ TYPICAL CHARACTERISTICS